



Vincotech

| MiniSKiiP® 1 PIM | 600 V / 6 A |
|--|--|
| <div style="border: 1px solid black; padding: 5px; margin-bottom: 5px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Features</p> <ul style="list-style-type: none"> Solderless interconnection Trench Fieldstop IGBT3 technology </div> <div style="border: 1px solid black; padding: 5px; margin-bottom: 5px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Target Applications</p> <ul style="list-style-type: none"> Industrial drives </div> <div style="border: 1px solid black; padding: 5px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Types</p> <ul style="list-style-type: none"> V23990-K201-A-PM </div> | <div style="border: 1px solid black; padding: 5px; margin-bottom: 5px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">MiniSKiiP® 1 housing</p> </div> <div style="border: 1px solid black; padding: 5px;"> <p style="text-align: center; background-color: #ccc; margin: 0;">Schematic</p> </div> |

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Condition | Value | Unit |
|--|----------------------|--|----------|------------------|
| Rectifier Diode | | | | |
| Repetitive peak reverse voltage | V_{RRM} | | 1600 | V |
| DC forward current | I_{FAV} | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 29 | A |
| Surge (non-repetitive) forward current | I_{FSM} | $t_p = 10\text{ ms}$ half sine wave | 220 | A |
| I ² t-value | I^2t | | 240 | A ² s |
| Power dissipation | P_{tot} | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 46 | W |
| Maximum Junction Temperature | T_{jmax} | | 150 | °C |
| Inverter Switch / Brake Switch | | | | |
| Collector-emitter breakdown voltage | V_{CE} | | 600 | V |
| DC collector current | I_C | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 10 | A |
| Repetitive peak collector current | I_{CRM} | t_p limited by T_{jmax} | 18 | A |
| Power dissipation | P_{tot} | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 40 | W |
| Gate-emitter peak voltage | V_{GE} | | ±20 | V |
| Short circuit ratings | t_{SC} V_{CC} | $T_j \leq 150\text{ °C}$ $V_{GE} = 15\text{ V}$ | 6 360 | μs V |
| Maximum Junction Temperature | T_{jmax} | | 175 | °C |



Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Condition | Value | Unit |
|-------------------------------------|------------|---------------------------------------|-------|------|
| Inverter Diode / Brake Diode | | | | |
| Repetitive peak reverse voltage | V_{RRM} | | 600 | V |
| DC forward current | I_F | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 10 | A |
| Repetitive peak forward current | I_{FRM} | t_p limited by T_{jmax} | 20 | A |
| Power dissipation | P_{tot} | $T_j = T_{jmax}$ $T_s = 80\text{ °C}$ | 31 | W |
| Maximum Junction Temperature | T_{jmax} | | 175 | °C |

Thermal Properties

| | | | | |
|---|-----------|--|----------------------------|----|
| Storage temperature | T_{stg} | | -40...+125 | °C |
| Operation temperature under switching condition | T_{op} | | -40...+($T_{jmax} - 25$) | °C |

Isolation Properties

| | | | | |
|----------------------------|----------|----------------------------------|----------|----|
| Isolation voltage | V_{is} | $t = 2\text{ s}$ DC Test Voltage | 4000 | V |
| Creepage distance | | | min 12,7 | mm |
| Clearance | | | min 12,7 | mm |
| Comparative Tracking Index | CTI | | >200 | |



Characteristic Values

| Parameter | Symbol | Conditions | | | | | Value | | | Unit | | | | |
|---|----------------------|---|--------------|-----------|--------------|--------------|-----------|-----------|-----------|------|------------------------|-------|--------|------------------|
| | | V_{GE} [V] | V_{GS} [V] | V_r [V] | V_{CE} [V] | V_{DS} [V] | I_C [A] | I_F [A] | I_D [A] | | T_j [°C] | Min | Typ | Max |
| Rectifier Diode | | | | | | | | | | | | | | |
| Forward voltage | V_F | | | | | 25 | 25 | 25 | | | 1,51 | 1,42 | | V |
| Threshold voltage (for power loss calc. only) | V_{to} | | | | | 25 | 25 | 25 | | | 0,86 | 0,79 | | V |
| Slope resistance (for power loss calc. only) | r_t | | | | | 25 | 25 | 25 | | | 0,03 | 0,03 | | Ω |
| Reverse current | I_r | | | | | 1500 | | | 25 | | | | 0,05 | mA |
| Thermal resistance junction to sink | $R_{th(j-s)}$ | Thermal grease thickness ≤ 50um $\lambda = 1$ W/mK | | | | | | | | | 1,50 | | | K/W |
| Inverter Switch / Brake Switch | | | | | | | | | | | | | | |
| Gate emitter threshold voltage | $V_{GE(th)}$ | $V_{CE} = V_{GE}$ | | | | 0,0008 | 25 | | | 5 | 2,8 | 6,5 | | V |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | | 15 | | | 6 | 25 | 150 | | 1,1 | 1,69 | 1,88 | 1,9 | V |
| Collector-emitter cut-off current incl. Diode | I_{CES} | | 0 | 600 | | | 25 | | | | | | 0,0004 | mA |
| Gate-emitter leakage current | I_{GES} | | 20 | 0 | | | 25 | | | | | | 300 | nA |
| Integrated Gate resistor | R_{gint} | | | | | | | | | | none | | | Ω |
| Turn-on delay time | $t_{d(on)}$ | $R_{goff} = 32 \Omega$ $R_{gon} = 64 \Omega$ | ± 15 | 300 | 6 | 25 | 25 | 25 | | | 21 | 20 | | ns |
| Rise time | t_r | | | | | 150 | 150 | 150 | | | 13 | 17 | | |
| Turn-off delay time | $t_{d(off)}$ | | | | | 25 | 25 | 25 | | | 152 | 170 | | |
| Fall time | t_f | | | | | 150 | 150 | 150 | | | 98 | 103 | | |
| Turn-on energy loss | E_{on} | | | | | 25 | 150 | 150 | | | 0,155 | 0,209 | | |
| Turn-off energy loss | E_{off} | 25 | 150 | 150 | | | 0,133 | 0,168 | | | | | mWs | |
| Input capacitance | C_{ies} | | | | | | | | | | 380 | | | pF |
| Output capacitance | C_{oss} | $f = 1$ MHz | 0 | 25 | | 25 | | | | | 28 | | | |
| Reverse transfer capacitance | C_{rss} | | | | | | | | | | 11 | | | |
| Thermal resistance junction to sink | $R_{th(j-s)}$ | Thermal grease thickness ≤ 50um $\lambda = 1$ W/mK | | | | | | | | | 2,40 | | | K/W |
| Inverter Diode / Brake Diode | | | | | | | | | | | | | | |
| Diode forward voltage | V_F | | | | | 50 | 25 | 150 | | | 1,34 | 1,34 | | V |
| Peak reverse recovery current | I_{RRM} | $di/dt = tbd$ A/us | | | | | 25 | 150 | | | 5,97 | 6,97 | | A |
| Reverse recovery time | t_{rr} | | 25 | 150 | 150 | | | 185 | 280 | | | | | ns |
| Reverse recovered charge | Q_{rr} | | 25 | 150 | 150 | | | 0,44 | 0,78 | | | | | μC |
| Peak rate of fall of recovery current | $(di_{rr}/dt)_{max}$ | | 25 | 150 | 150 | | | 115 | 37 | | | | | A/μs |
| Reverse recovered energy | E_{rec} | | 25 | 150 | 150 | | | 0,082 | 0,154 | | | | | mWs |
| Thermal resistance junction to sink | $R_{th(j-s)}$ | Thermal grease thickness ≤ 50um $\lambda = 1$ W/mK | | | | | | | | | 3,00 | | | K/W |
| Thermistor | | | | | | | | | | | | | | |
| Rated resistance | R | | | | | | 25 | | | | 1000 | | | Ω |
| Deviation of R_{100} | $\Delta_{R/R}$ | $R_{100} = 1670 \Omega$ | | | | | 100 | | -3 | | | 3 | | % |
| R_{100} | R | | | | | | 100 | | | | 1670 | | | Ω |
| Power dissipation constant | | | | | | | 25 | | | | | | | mW/K |
| A-value | $B_{(25/50)}$ | | | | | | 25 | | | | 7,635*10 ⁻³ | | | 1/K |
| B-value | $B_{(25/100)}$ | | | | | | 25 | | | | 1,731*10 ⁻⁵ | | | 1/K ² |
| Vincotech NTC Reference | | | | | | | | | | | | | E | |



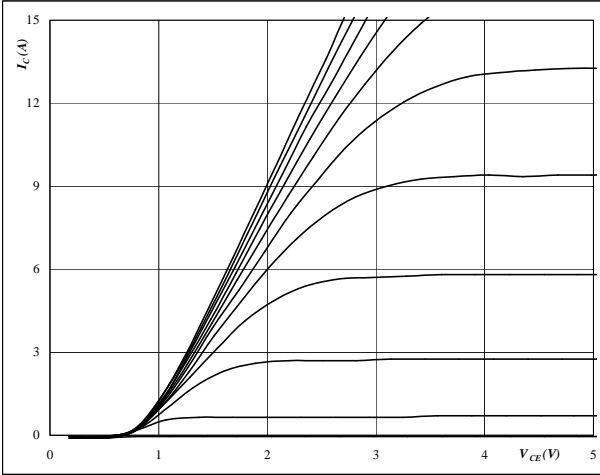
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Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$



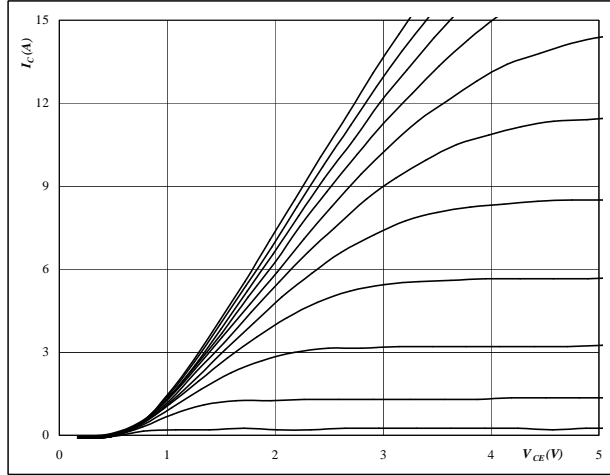
At

$t_p = 250 \mu s$
 $T_j = 25 \text{ } ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$



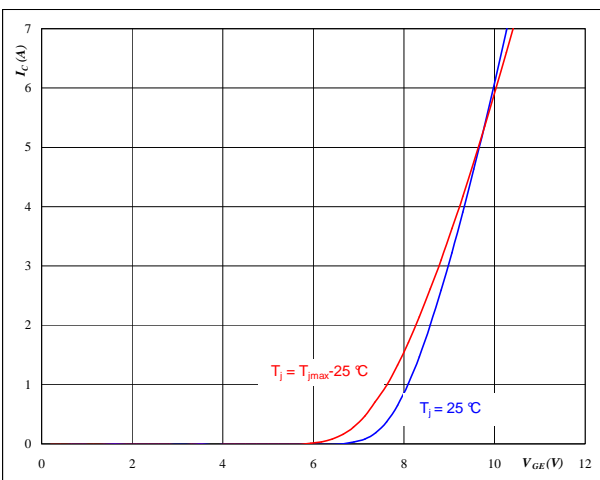
At

$t_p = 250 \mu s$
 $T_j = 125 \text{ } ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$



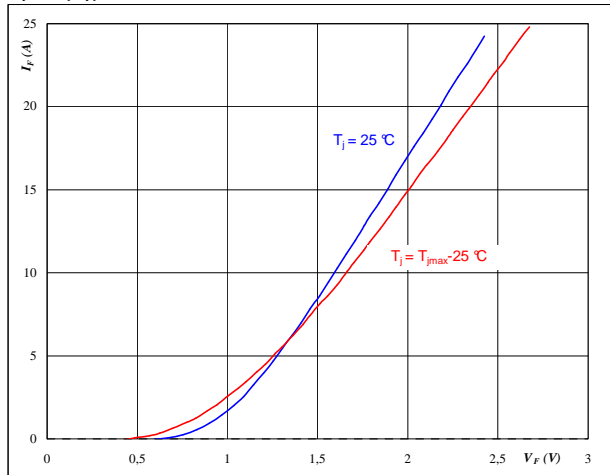
At

$t_p = 250 \mu s$
 $V_{CE} = 10 \text{ V}$

figure 4. FWD

Typical diode forward current as a function of forward voltage

$$I_F = f(V_F)$$



At

$t_p = 250 \mu s$



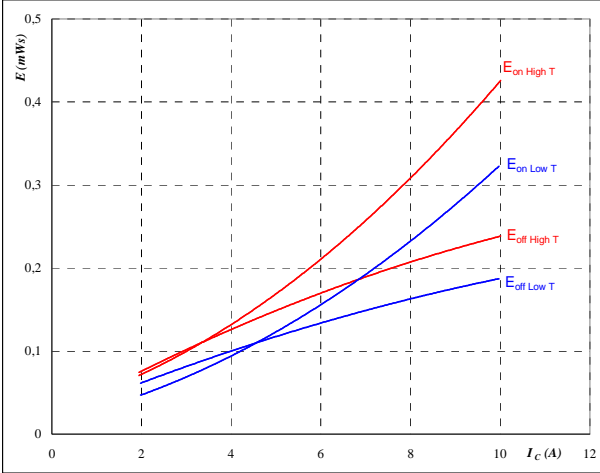
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Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 5. IGBT

Typical switching energy losses
as a function of collector current

$$E = f(I_C)$$



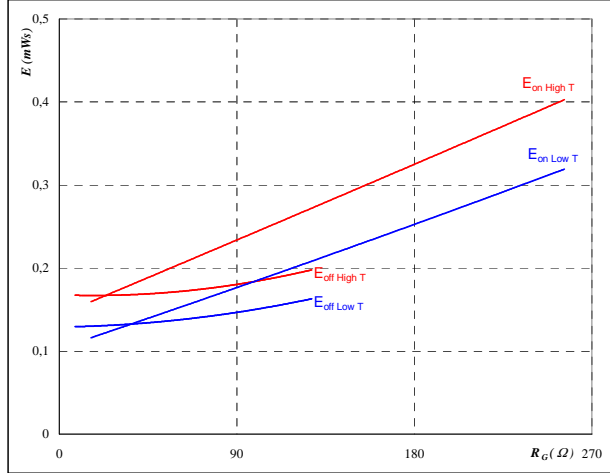
With an inductive load at

$T_j = 25/125$ °C
 $V_{CE} = 300$ V
 $V_{GE} = 15$ V
 $R_{gon} = 64$ Ω
 $R_{goff} = 32$ Ω

figure 6. IGBT

Typical switching energy losses
as a function of gate resistor

$$E = f(R_G)$$



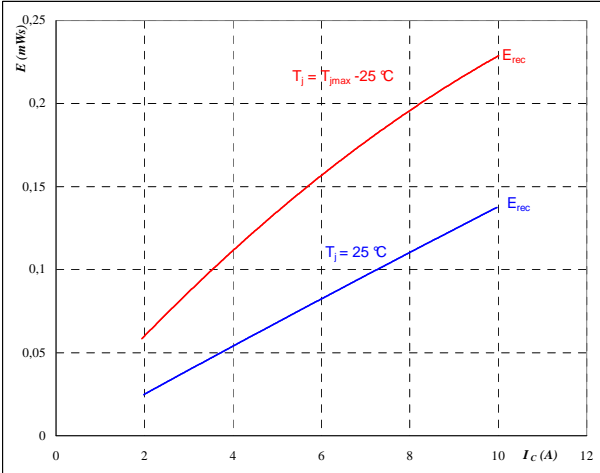
With an inductive load at

$T_j = 25/125$ °C
 $V_{CE} = 300$ V
 $V_{GE} = 15$ V
 $I_C = 6$ A

figure 7. FWD

Typical reverse recovery energy loss
as a function of collector current

$$E_{rec} = f(I_C)$$



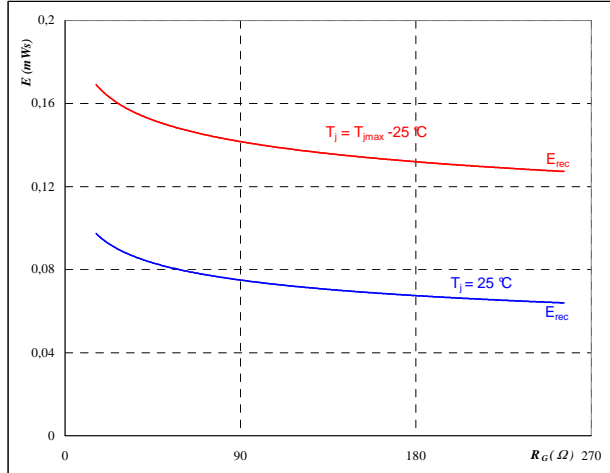
With an inductive load at

$T_j = 25/125$ °C
 $V_{CE} = 300$ V
 $V_{GE} = 15$ V
 $R_{gon} = 64$ Ω

figure 8. FWD

Typical reverse recovery energy loss
as a function of gate resistor

$$E_{rec} = f(R_G)$$



With an inductive load at

$T_j = 25/125$ °C
 $V_{CE} = 300$ V
 $V_{GE} = 15$ V
 $I_C = 6$ A



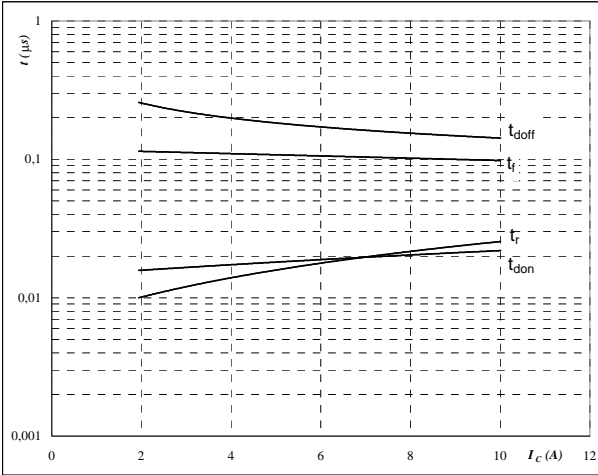
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Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 9. IGBT

Typical switching times as a function of collector current

$$t = f(I_C)$$



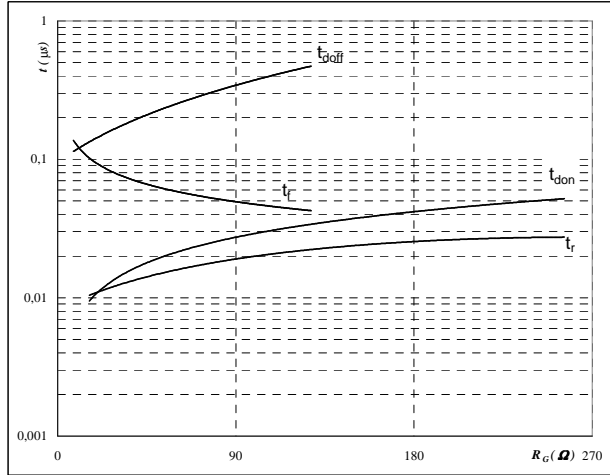
With an inductive load at

| | | |
|--------------|-----|----------|
| $T_j =$ | 125 | °C |
| $V_{CE} =$ | 300 | V |
| $V_{GE} =$ | 15 | V |
| $R_{gon} =$ | 64 | Ω |
| $R_{goff} =$ | 32 | Ω |

figure 10. IGBT

Typical switching times as a function of gate resistor

$$t = f(R_G)$$



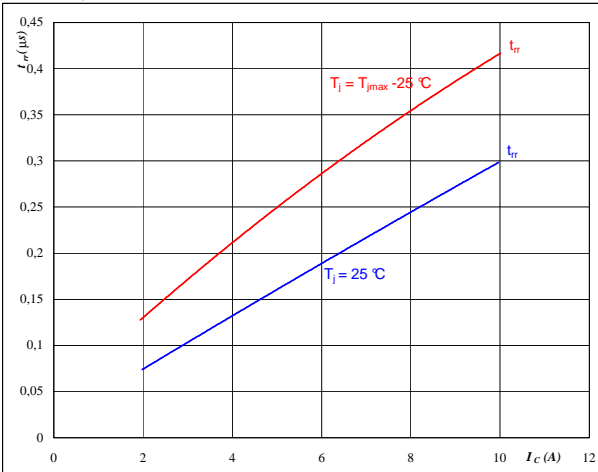
With an inductive load at

| | | |
|------------|-----|----|
| $T_j =$ | 125 | °C |
| $V_{CE} =$ | 300 | V |
| $V_{GE} =$ | 15 | V |
| $I_C =$ | 6 | A |

figure 11. FWD

Typical reverse recovery time as a function of collector current

$$t_{rr} = f(I_C)$$



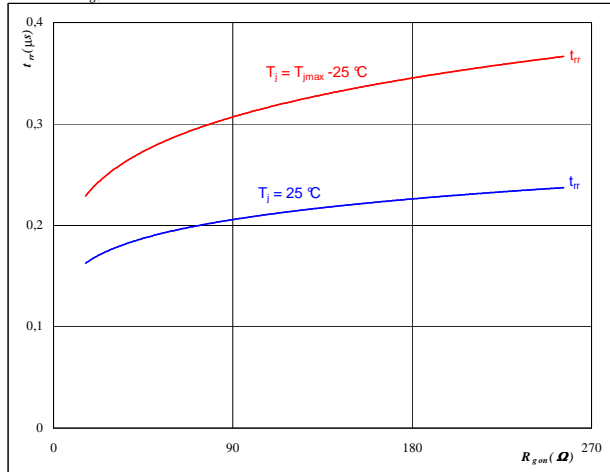
At

| | | |
|-------------|--------|----------|
| $T_j =$ | 25/125 | °C |
| $V_{CE} =$ | 300 | V |
| $V_{GE} =$ | 15 | V |
| $R_{gon} =$ | 64 | Ω |

figure 12. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$$t_{rr} = f(R_{gon})$$



At

| | | |
|------------|--------|----|
| $T_j =$ | 25/125 | °C |
| $V_R =$ | 300 | V |
| $I_F =$ | 6 | A |
| $V_{GE} =$ | 15 | V |



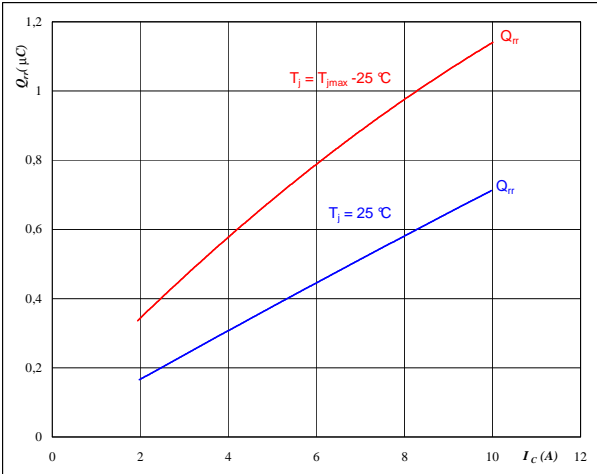
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Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 13. FWD

Typical reverse recovery charge as a function of collector current

$$Q_{rr} = f(I_C)$$



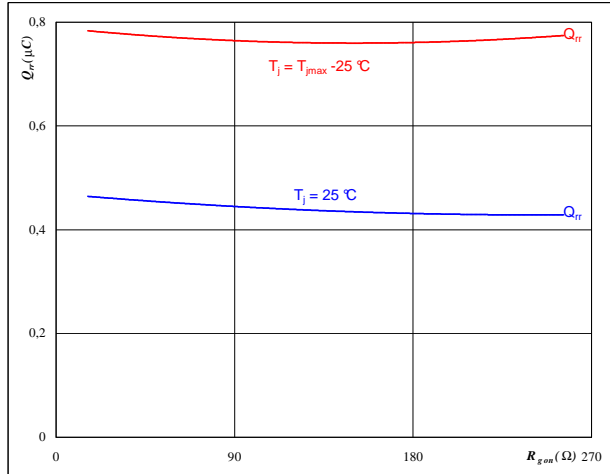
At

$T_j = 25/125\text{ °C}$
 $V_{CE} = 300\text{ V}$
 $V_{GE} = 15\text{ V}$
 $R_{gon} = 64\text{ }\Omega$

figure 14. FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$$Q_{rr} = f(R_{gon})$$



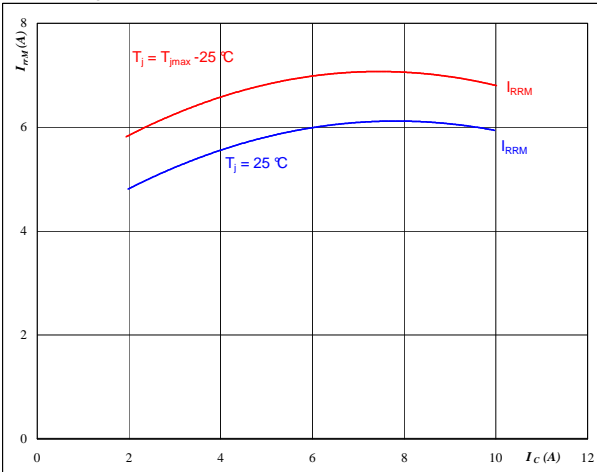
At

$T_j = 25/125\text{ °C}$
 $V_R = 300\text{ V}$
 $I_F = 6\text{ A}$
 $V_{GE} = 15\text{ V}$

figure 15. FWD

Typical reverse recovery current as a function of collector current

$$I_{RRM} = f(I_C)$$



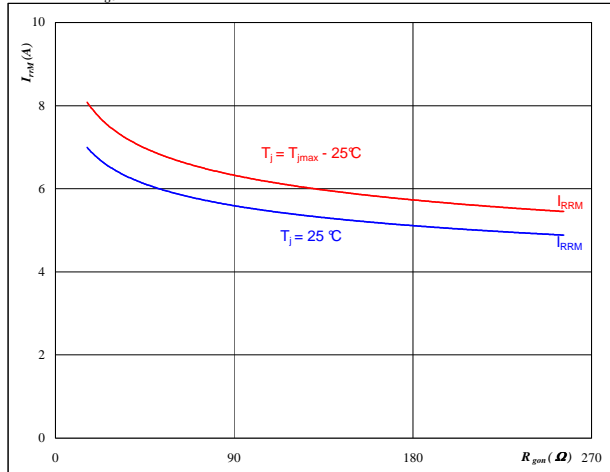
At

$T_j = 25/125\text{ °C}$
 $V_{CE} = 300\text{ V}$
 $V_{GE} = 15\text{ V}$
 $R_{gon} = 64\text{ }\Omega$

figure 16. FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RRM} = f(R_{gon})$$



At

$T_j = 25/125\text{ °C}$
 $V_R = 300\text{ V}$
 $I_F = 6\text{ A}$
 $V_{GE} = 15\text{ V}$



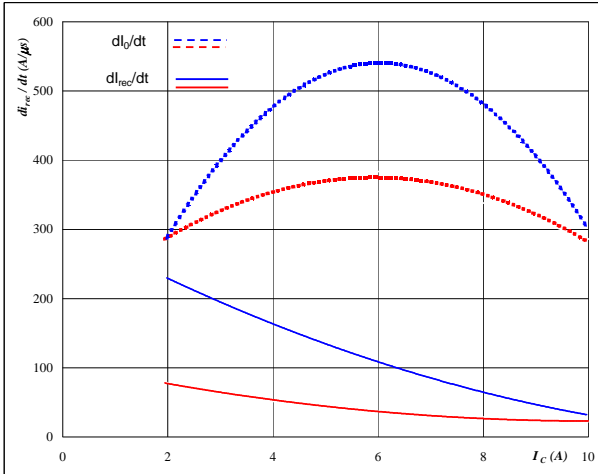
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Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 17. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$$dI_0/dt, dI_{rec}/dt = f(I_C)$$

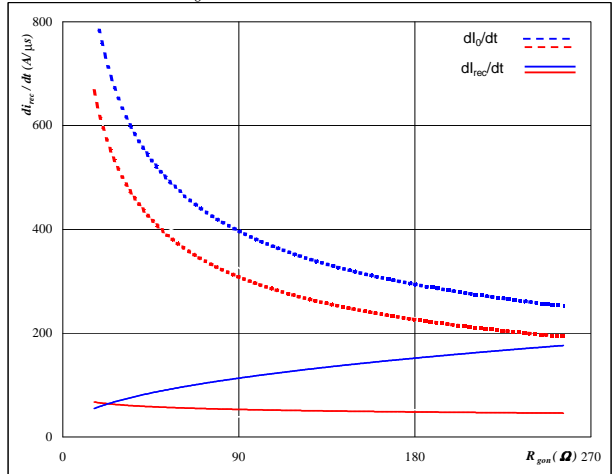


At
 $T_j = 25/125$ °C
 $V_{CE} = 300$ V
 $V_{GE} = 15$ V
 $R_{gon} = 64$ Ω

figure 18. FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$$dI_0/dt, dI_{rec}/dt = f(R_{gon})$$

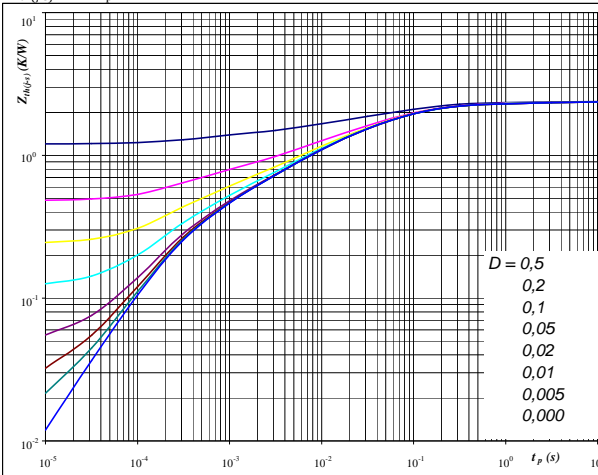


At
 $T_j = 25/125$ °C
 $V_R = 300$ V
 $I_F = 6$ A
 $V_{GE} = 15$ V

figure 19. IGBT

IGBT transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



At
 $D = t_p / T$
 $R_{th(j-s)} = 2,40$ K/W

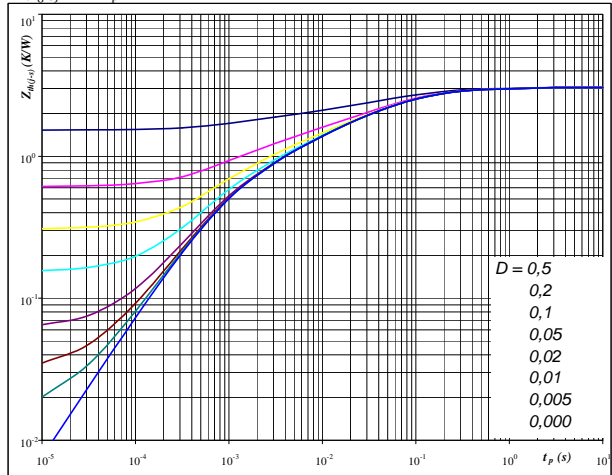
IGBT thermal model values

| R (K/W) | Tau (s) |
|----------|----------|
| 8,29E-02 | 9,69E+00 |
| 1,83E-01 | 4,83E-01 |
| 8,23E-01 | 7,46E-02 |
| 5,86E-01 | 1,54E-02 |
| 4,26E-01 | 2,86E-03 |
| 2,99E-01 | 2,96E-04 |

figure 20. FWD

FWD transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



At
 $D = t_p / T$
 $R_{th(j-s)} = 3,00$ K/W

FWD thermal model values

| R (K/W) | Tau (s) |
|----------|----------|
| 1,66E-01 | 1,20E+00 |
| 8,73E-01 | 1,09E-01 |
| 9,47E-01 | 2,57E-02 |
| 5,64E-01 | 4,64E-03 |
| 5,02E-01 | 8,37E-04 |



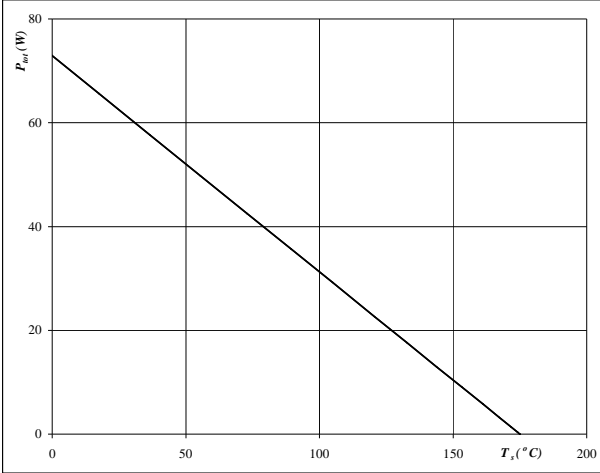
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Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 21. IGBT

Power dissipation as a function of heatsink temperature

$$P_{tot} = f(T_s)$$

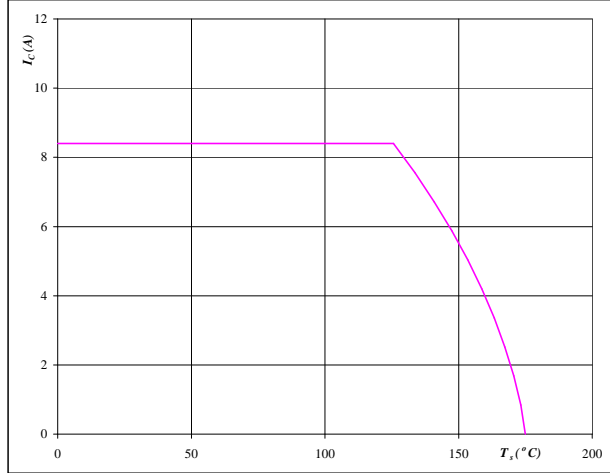


At
 $T_j = 175 \text{ } ^{\circ}C$

figure 22. IGBT

Collector current as a function of heatsink temperature

$$I_C = f(T_s)$$

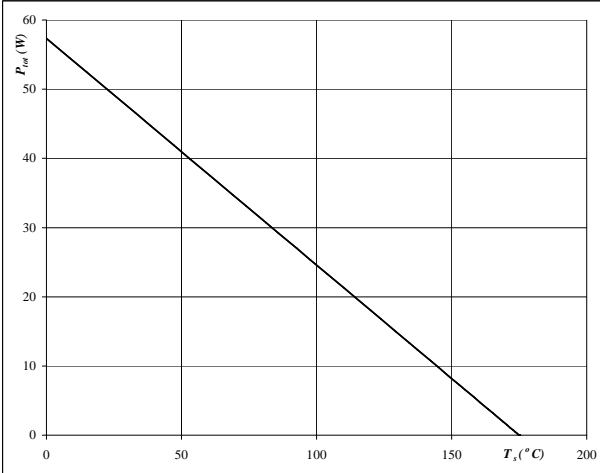


At
 $T_j = 175 \text{ } ^{\circ}C$
 $V_{GE} = 15 \text{ V}$

figure 23. FWD

Power dissipation as a function of heatsink temperature

$$P_{tot} = f(T_s)$$

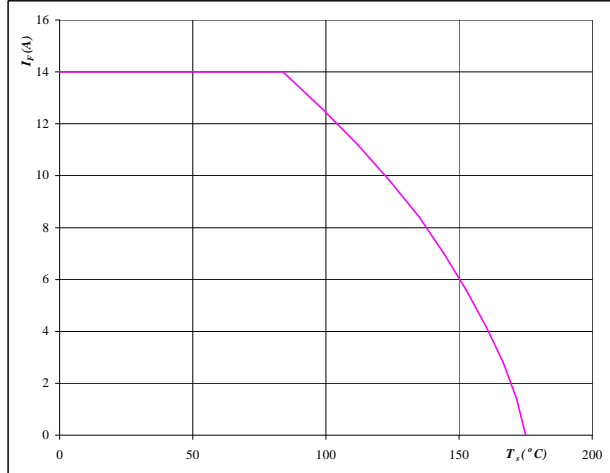


At
 $T_j = 175 \text{ } ^{\circ}C$

figure 24. FWD

Forward current as a function of heatsink temperature

$$I_F = f(T_s)$$



At
 $T_j = 175 \text{ } ^{\circ}C$



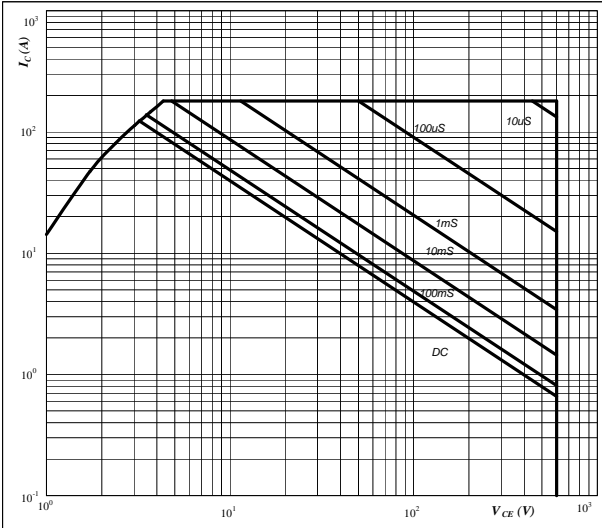
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Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 25. IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$

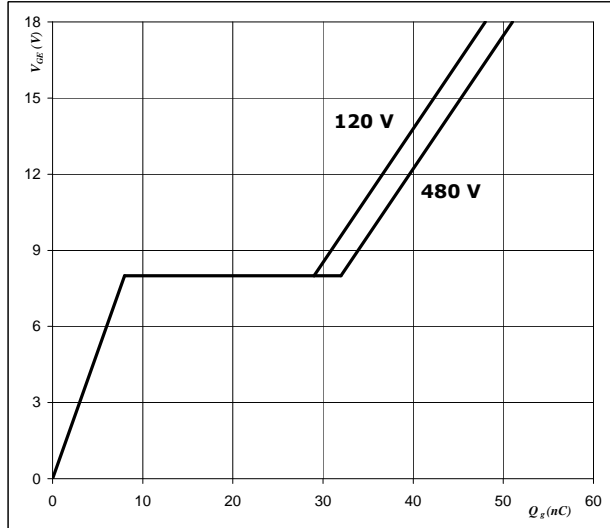


At
 D = single pulse
 T_s = 80 °C
 V_{GE} = 15 V
 T_j = T_{jmax}

figure 26. IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Q_g)$



At
 I_C = 6 A

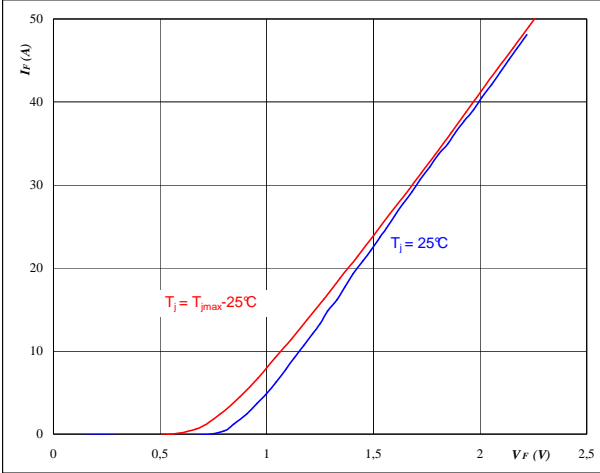


Rectifier Diode

figure 1. Rectifier Diode

Typical diode forward current as a function of forward voltage

$$I_F = f(V_F)$$

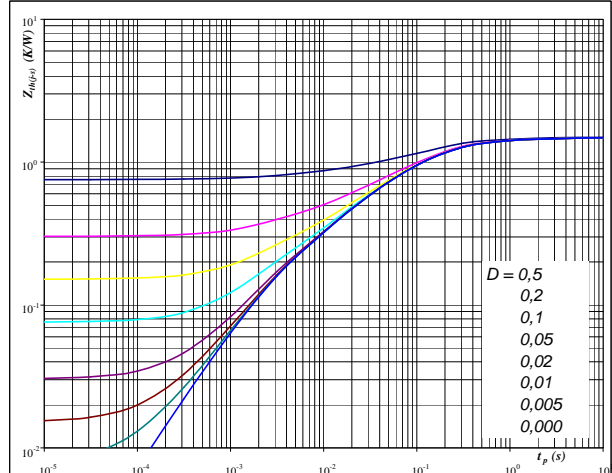


At
 $t_p = 250 \mu s$

figure 2. Rectifier Diode

Diode transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$

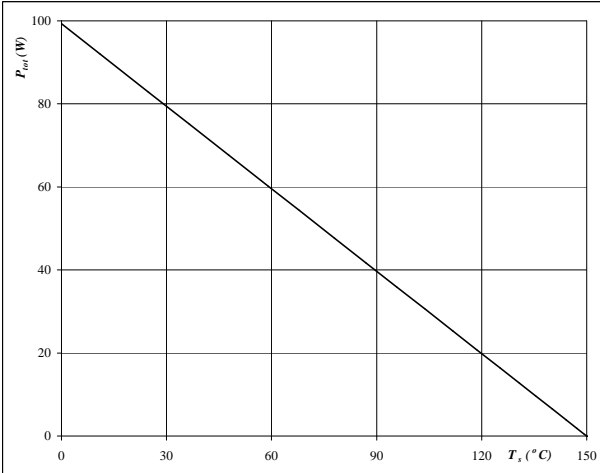


At
 $D = t_p / T$
 $R_{th(j-s)} = 1,50 \text{ K/W}$

figure 3. Rectifier Diode

Power dissipation as a function of heatsink temperature

$$P_{tot} = f(T_s)$$

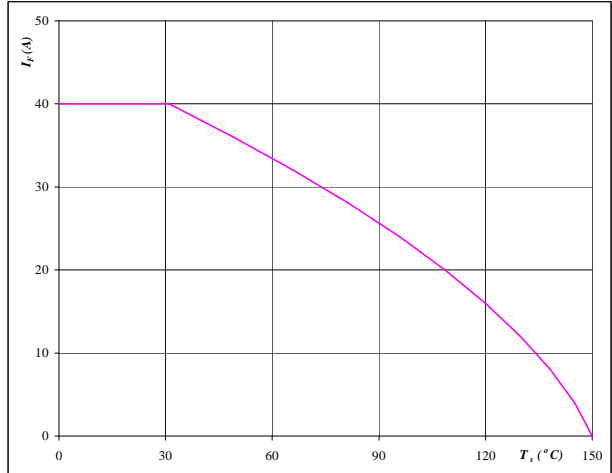


At
 $T_j = 150 \text{ °C}$

figure 4. Rectifier Diode

Forward current as a function of heatsink temperature

$$I_F = f(T_s)$$



At
 $T_j = 150 \text{ °C}$

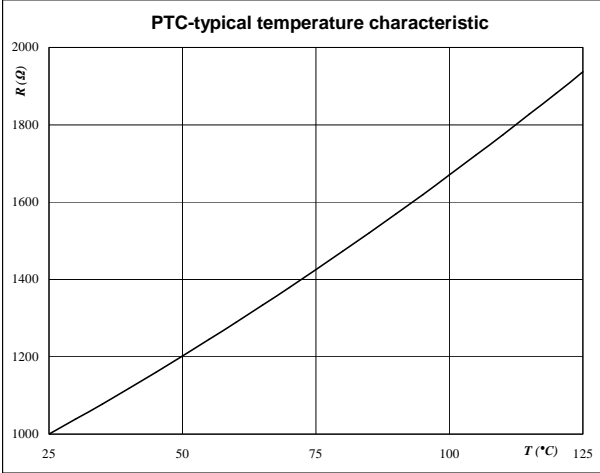


Thermistor

figure 1. Thermistor

**Typical PTC characteristic
as a function of temperature**

$$R = f(T)$$





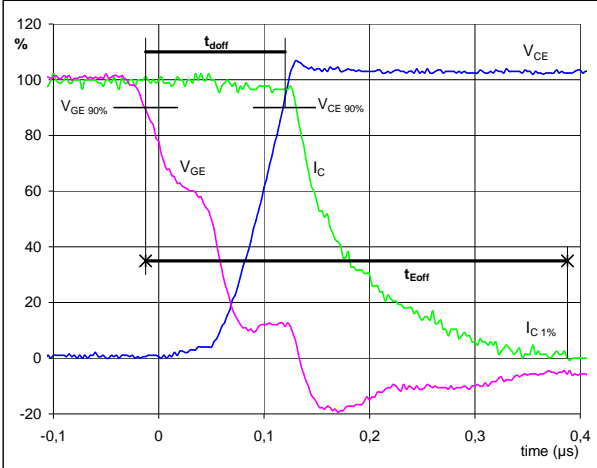
Switching Definitions Output Inverter

General conditions

| | | |
|------------|---|--------|
| T_j | = | 150 °C |
| R_{gon} | = | 32 Ω |
| R_{goff} | = | 17 Ω |

figure 1. IGBT

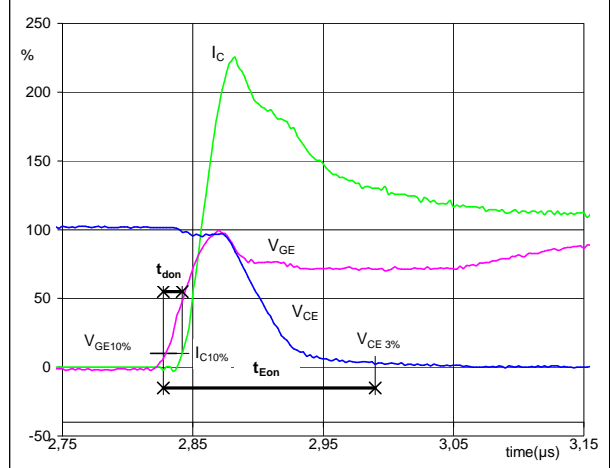
Turn-off Switching Waveforms & definition of t_{doff} t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



| | | |
|-------------------|------|----|
| V_{GE} (0%) = | 0 | V |
| V_{GE} (100%) = | 15 | V |
| V_C (100%) = | 300 | V |
| I_C (100%) = | 6 | A |
| t_{doff} = | 0,13 | μs |
| t_{Eoff} = | 0,40 | μs |

figure 2. IGBT

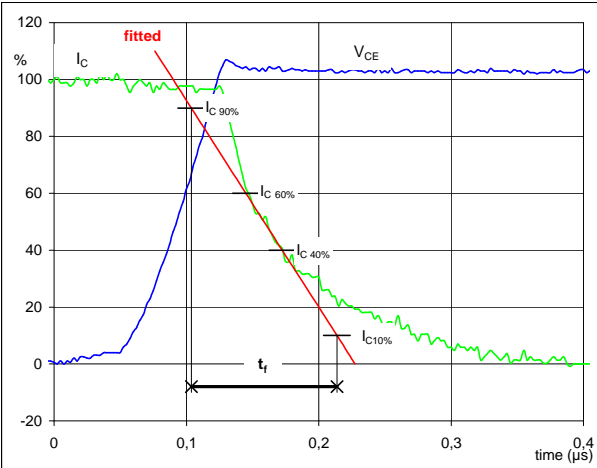
Turn-on Switching Waveforms & definition of t_{don} t_{Eon}
(t_{Eon} = integrating time for E_{on})



| | | |
|-------------------|------|----|
| V_{GE} (0%) = | 0 | V |
| V_{GE} (100%) = | 15 | V |
| V_C (100%) = | 300 | V |
| I_C (100%) = | 6 | A |
| t_{don} = | 0,01 | μs |
| t_{Eon} = | 0,16 | μs |

figure 3. IGBT

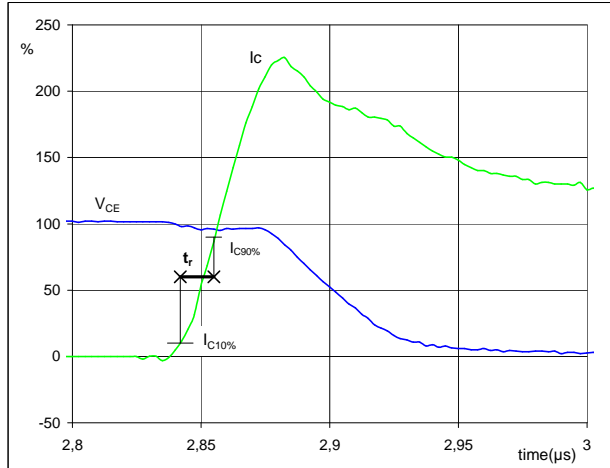
Turn-off Switching Waveforms & definition of t_f



| | | |
|----------------|------|----|
| V_C (100%) = | 300 | V |
| I_C (100%) = | 6 | A |
| t_f = | 0,10 | μs |

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

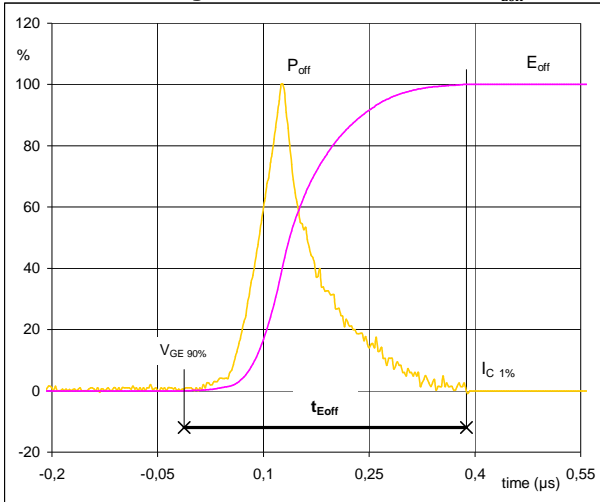


| | | |
|----------------|------|----|
| V_C (100%) = | 300 | V |
| I_C (100%) = | 6 | A |
| t_r = | 0,01 | μs |



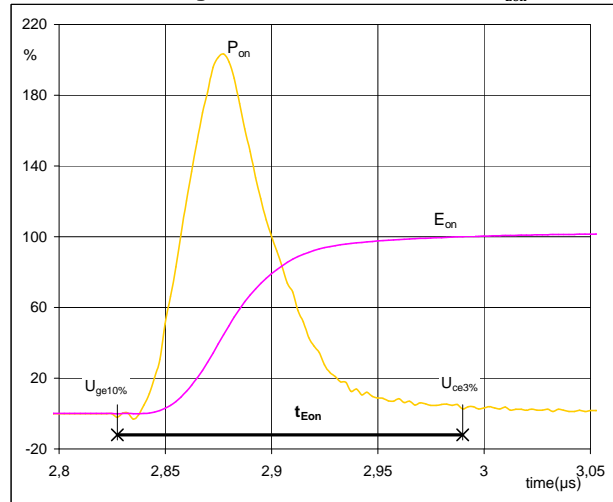
Switching Definitions Output Inverter

figure 5. IGBT
Turn-off Switching Waveforms & definition of t_{Eoff}



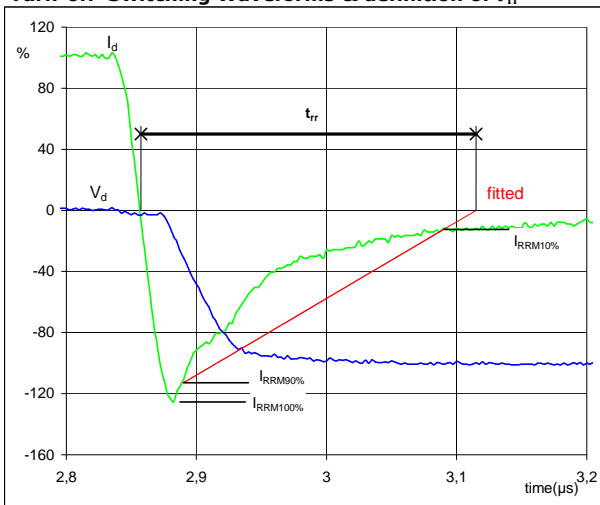
$P_{off} (100\%) = 1,80 \text{ kW}$
 $E_{off} (100\%) = 0,17 \text{ mJ}$
 $t_{Eoff} = 0,40 \text{ } \mu\text{s}$

figure 6. IGBT
Turn-on Switching Waveforms & definition of t_{Eon}



$P_{on} (100\%) = 1,80 \text{ kW}$
 $E_{on} (100\%) = 0,18 \text{ mJ}$
 $t_{Eon} = 0,16 \text{ } \mu\text{s}$

figure 7. IGBT
Turn-off Switching Waveforms & definition of t_{rr}



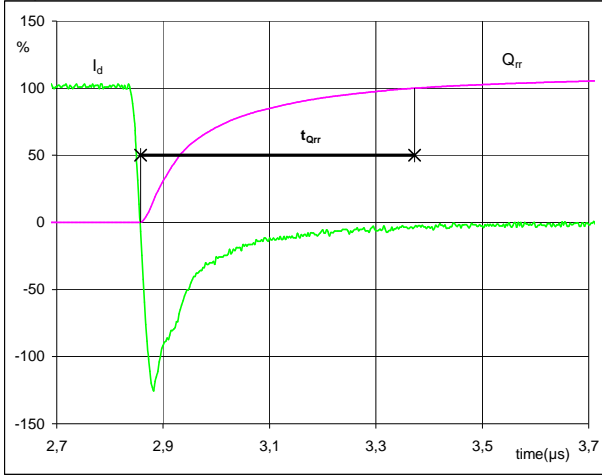
$V_d (100\%) = 300 \text{ V}$
 $I_d (100\%) = 6 \text{ A}$
 $I_{RRM} (100\%) = 7 \text{ A}$
 $t_{rr} = 0,25 \text{ } \mu\text{s}$



Switching Definitions Output Inverter

figure 8. FWD

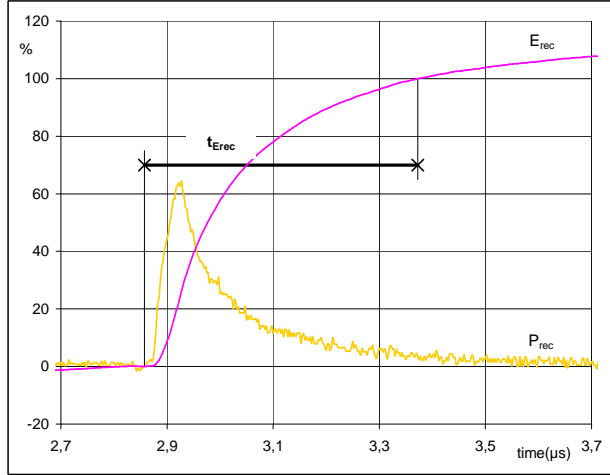
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



| | | |
|-------------------|------|---------------|
| I_d (100%) = | 6 | A |
| Q_{rr} (100%) = | 0,77 | μC |
| t_{Qrr} = | 0,51 | μs |

figure 9. FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec} = integrating time for E_{rec})



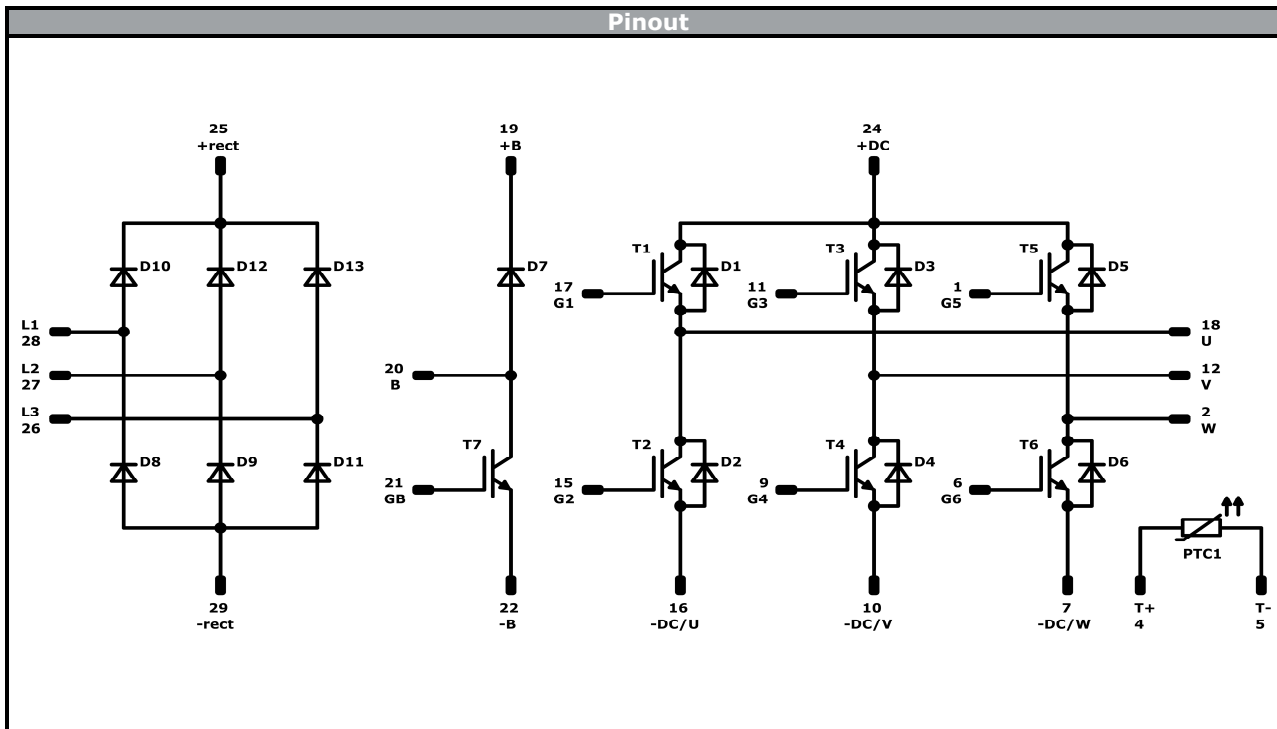
| | | |
|--------------------|------|---------------|
| P_{rec} (100%) = | 1,80 | kW |
| E_{rec} (100%) = | 0,16 | mJ |
| t_{Erec} = | 0,51 | μs |



| Ordering Code & Marking | | | | | | | |
|---|------------|----------|-----------------------|----------|-----------|------|--------|
| Version | | | Ordering Code | | | | |
| with std lid (black V23990-K12-T-PM) | | | V23990-K201-A-/0A/-PM | | | | |
| with std lid (black V23990-K12-T-PM) and P12 | | | V23990-K201-A-/1A/-PM | | | | |
| with thin lid (white V23990-K13-T-PM) | | | V23990-K201-A-/0B/-PM | | | | |
| with thin lid (white V23990-K13-T-PM) and P12 | | | V23990-K201-A-/1B/-PM | | | | |
| | Text | VIN | Date code | Name&Ver | UL | Lot | Serial |
| | | VIN | WWYY | NNNNVVV | UL | LLLL | SSSS |
| | Datamatrix | Type&Ver | Lot number | Serial | Date code | | |
| | | TTTTTIV | LLLL | SSSS | WWYY | | |

| Pad table [mm] | | | |
|----------------|---------------|-------|----------|
| Pad | X | Y | Function |
| 1 | 15,93 | -14,6 | G5 |
| 2 | 15,93 | -9,8 | W |
| 3 | Not assembled | | |
| 4 | 15,93 | -0,2 | +T |
| 5 | 15,93 | 7,62 | -T |
| 6 | 15,93 | 12,62 | G6 |
| 7 | 15,93 | 15,8 | -DC/W |
| 8 | Not assembled | | |
| 9 | 8,23 | 12,62 | G4 |
| 10 | 8,23 | 15,8 | -DC/V |
| 11 | 7,73 | -14,6 | G3 |
| 12 | 7,73 | -9,8 | V |
| 13 | Not assembled | | |
| 14 | Not assembled | | |
| 15 | 0,53 | 12,62 | G2 |
| 16 | 0,53 | 15,8 | -DC/U |
| 17 | -0,47 | -14,6 | G1 |
| 18 | -0,47 | -9,8 | U |
| 19 | -5,47 | -5 | +B |
| 20 | -5,47 | 5,35 | B |
| 21 | -7,17 | 12,62 | GB |
| 22 | -7,17 | 15,8 | -B |
| 23 | Not assembled | | |
| 24 | -8,07 | -9,8 | +DC |
| 25 | -15,02 | -15,8 | +RECT |
| 26 | -15,02 | -9,8 | L3 |
| 27 | -15,02 | 0 | L2 |
| 28 | -15,02 | 9,8 | L1 |
| 29 | -15,02 | 15,8 | -RECT |

Pad positions refers to center point. For more informations on pad design please see package data.




| Identification | | | | | |
|-----------------------|-----------|---------|---------|-----------------|---------|
| ID | Component | Voltage | Current | Function | Comment |
| D8-D13 | Rectifier | 1600 V | 25 A | Rectifier Diode | |
| T1-T6 | IGBT | 600 V | 6 A | Inverter Switch | |
| D1-D6 | FWD | 600 V | 10 A | Inverter Diode | |
| T7 | IGBT | 600 V | 6 A | Brake Switch | |
| D7 | FWD | 600 V | 10 A | Brake Diode | |
| PTC1 | PTC | | | Thermistor | |



| Packaging instruction | | | |
|-----------------------------------|------------|---------------|-------------|
| Standard packaging quantity (SPQ) | 120 | >SPQ Standard | <SPQ Sample |

| Handling instruction |
|--|
| Handling instructions for MiniSkiiP® 1 packages see vincotech.com website. |

| Package data |
|---|
| Package data for MiniSkiiP® 1 packages see vincotech.com website. |

| UL recognition and file number |
|---|
| This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.  |

| Document No.: | Date: | Modification: | Pages |
|---------------------|--------------|---------------|-------|
| V23990-K201-A-D4-14 | 27 Jul. 2016 | | |

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.